

SPECIFICATION OF LED CHIP

C1050-30

[NIR]

1) Commodity Type and Physical Characteristics.

- 1. Material InGaAsP/InP
- 2. Electrode Top Side P (anode) side : Au Alloy
Bottom Side N (cathode) side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

| parameters | symbol | condition | min. | typ. | max. | unit |
|------------------------------|-----------------|-----------|------|------|------|------|
| Forward Voltage | Vf | If=20mA | | 1.1 | 1.4 | V |
| Reverse Current | Ir | Vr=3V | | | 10 | uA |
| Power Intensity | Po | If=20mA | | 0.6 | | mW |
| Peak Wavelength | λ_P | If=20mA | | 1050 | | nm |
| Spectral Radiation Bandwidth | $\Delta\lambda$ | If=20mA | | 60 | | nm |
| RiseTime | tr | If=20mA | | 20 | | ns |
| FallTime | tf | If=20mA | | 20 | | ns |

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

‡ Power intensity is measured by PD G8370-85. (Ta=25°C)

[Unit: um]

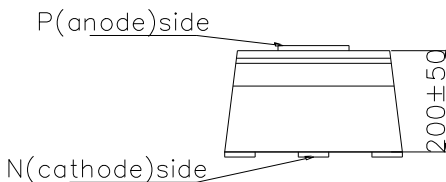
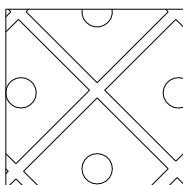
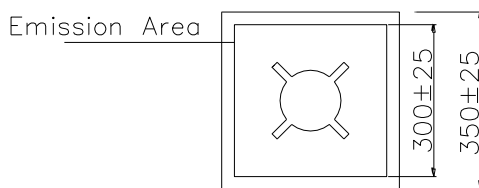
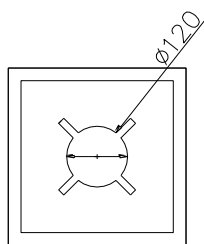


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area